

One Watt Darlington Transistors

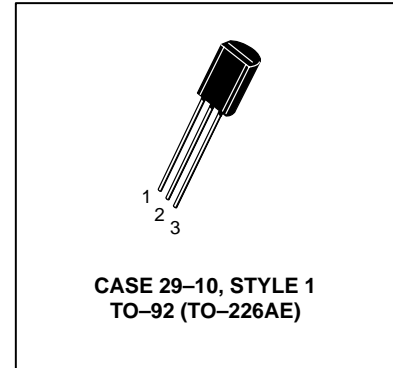
NPN Silicon

MPSW45 MPSW45A*

*ON Semiconductor Preferred Device

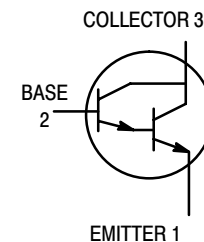
MAXIMUM RATINGS

Rating	Symbol	MPSW45	MPSW45A	Unit
Collector–Emitter Voltage	V_{CES}	40	50	Vdc
Collector–Base Voltage	V_{CBO}	50	60	Vdc
Emitter–Base Voltage	V_{EBO}	12	12	Vdc
Collector Current — Continuous	I_C	1.0	1.0	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0	8.0	Watts mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5	20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 100 \mu\text{Adc}, V_{BE} = 0$)	MPSW45 MPSW45A	$V_{(BR)CES}$	40 50	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	MPSW45 MPSW45A	$V_{(BR)CBO}$	50 60	— —	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)		$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{Vdc}, I_E = 0$) ($V_{CB} = 40 \text{Vdc}, I_E = 0$)	MPSW45 MPSW45A	I_{CBO}	— —	100 100	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{Vdc}, I_C = 0$)		I_{EBO}	—	100	nAdc

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MPSW45 MPSW45A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS⁽¹⁾				
DC Current Gain ($I_C = 200\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	25,000 15,000 4,000	150,000 — —	—
Collector–Emitter Saturation Voltage ($I_C = 1.0\text{ Adc}$, $I_B = 2.0\text{ mAdc}$)	$V_{CE(sat)}$	—	1.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 1.0\text{ Adc}$, $I_B = 2.0\text{ mAdc}$)	$V_{BE(sat)}$	—	2.0	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	—	2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 200\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	—	MHz
Collector–Base Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	—	6.0	pF

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

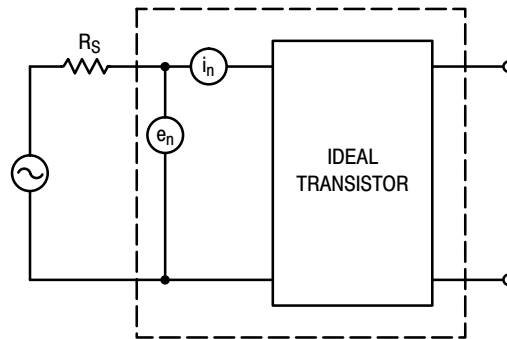


Figure 1. Transistor Noise Model

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NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

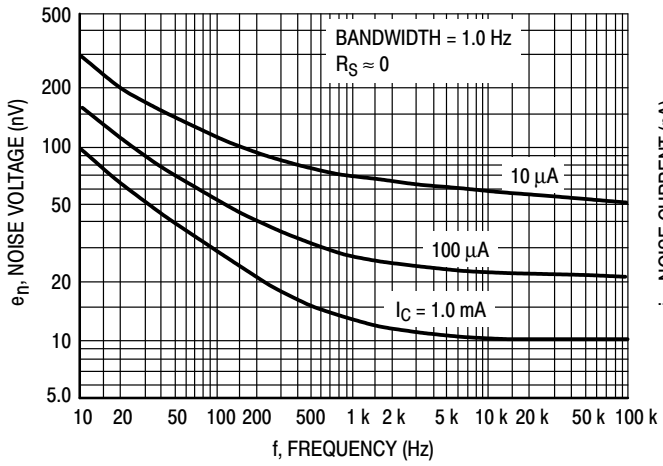


Figure 2. Noise Voltage

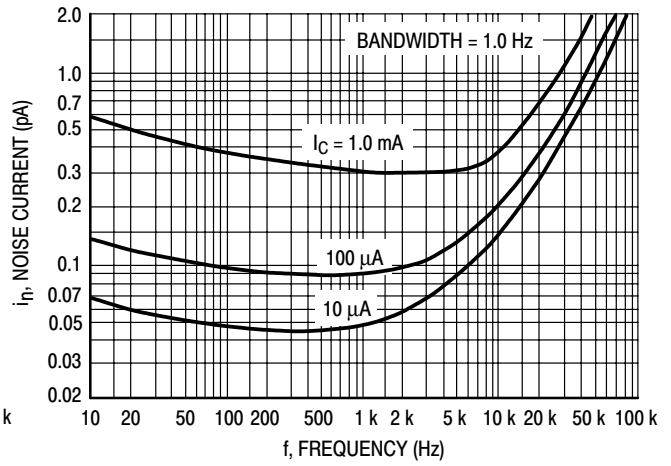


Figure 3. Noise Current

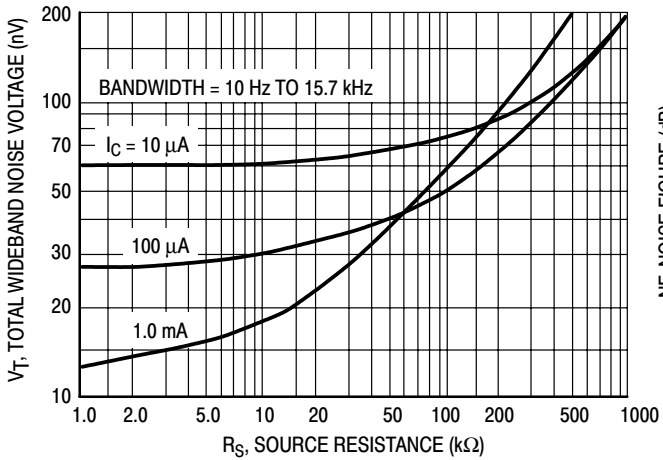


Figure 4. Total Wideband Noise Voltage

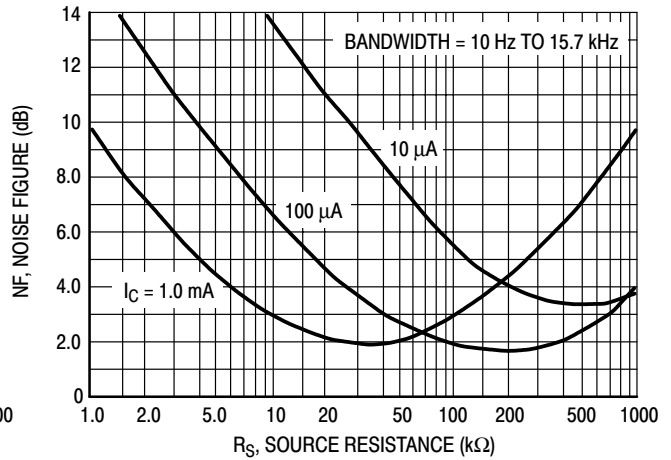


Figure 5. Wideband Noise Figure

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SMALL-SIGNAL CHARACTERISTICS

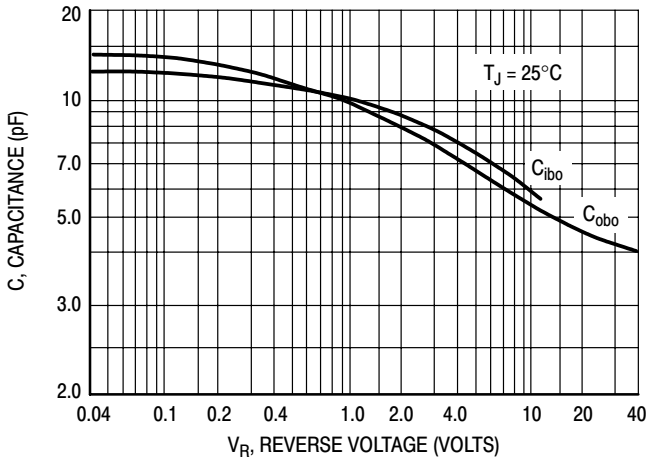


Figure 6. Capacitance

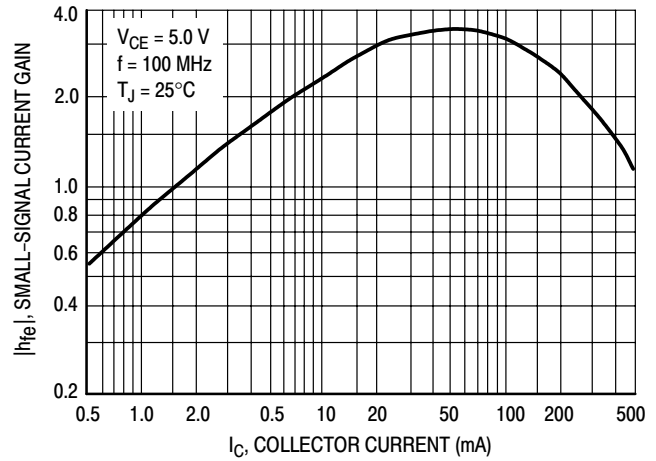


Figure 7. High Frequency Current Gain

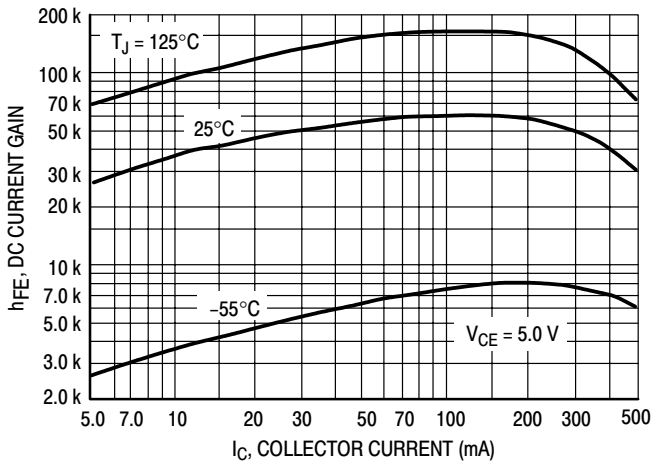


Figure 8. DC Current Gain

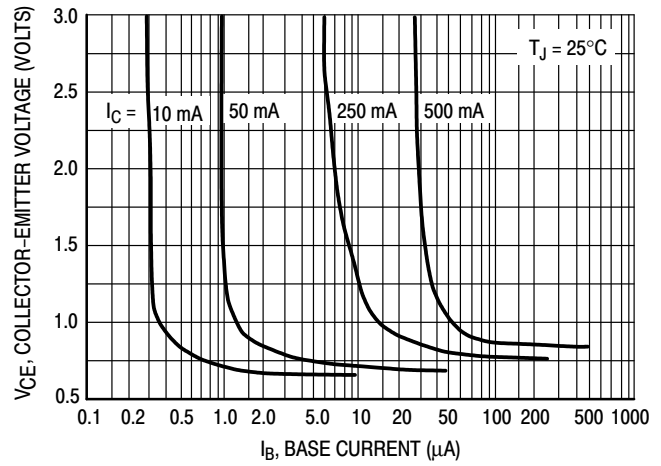


Figure 9. Collector Saturation Region

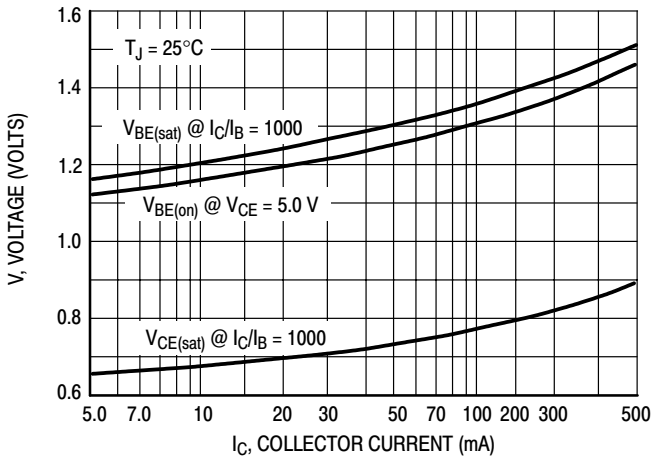


Figure 10. "On" Voltages

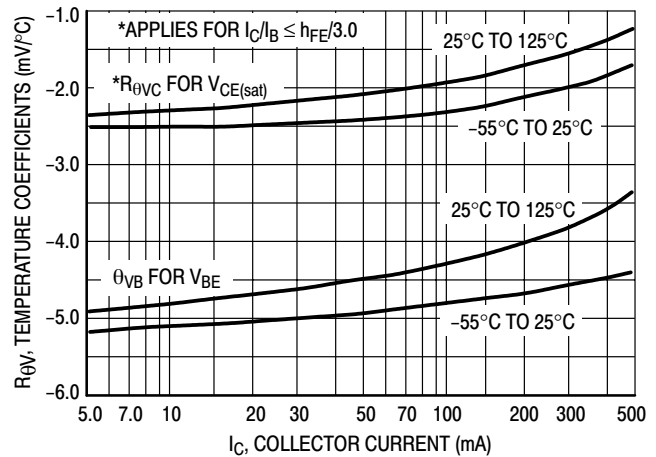


Figure 11. Temperature Coefficients

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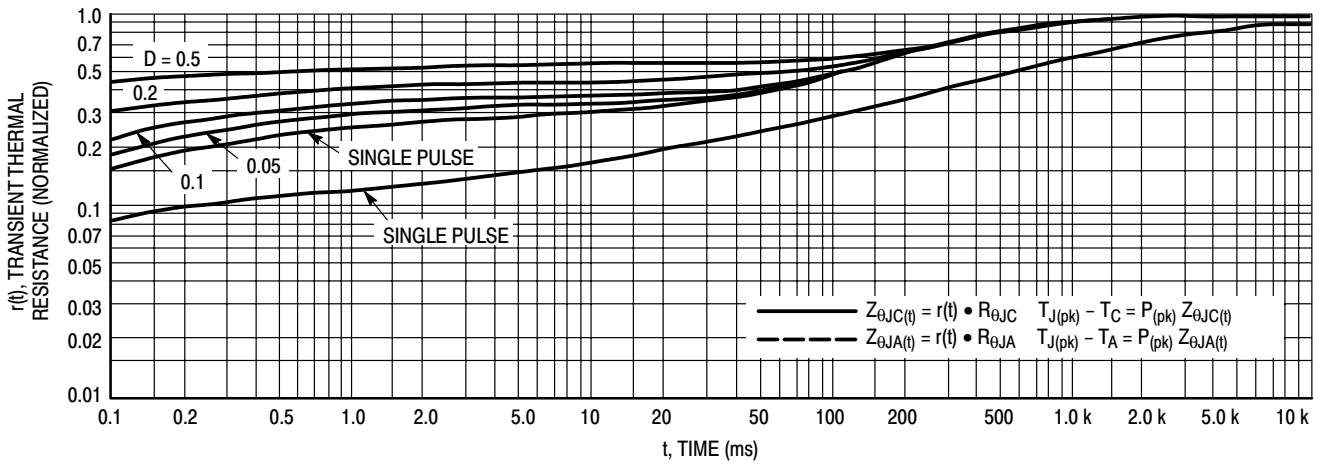


Figure 12. Thermal Response

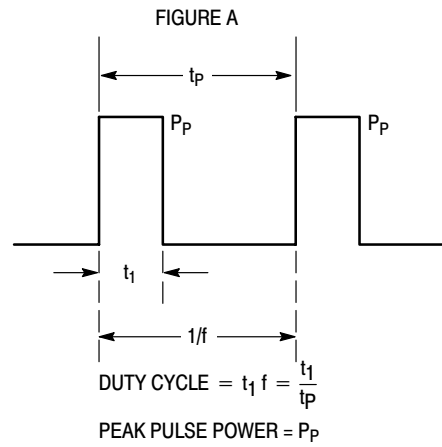
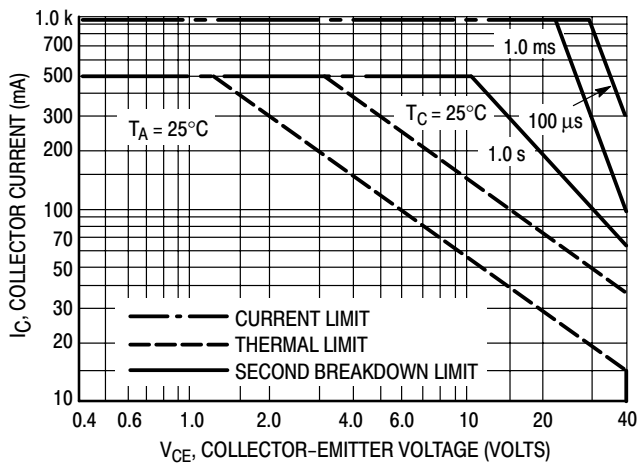
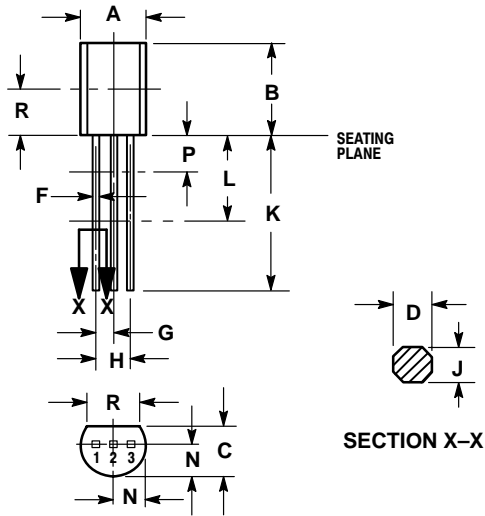


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data

MPSW45 MPSW45A

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-10
ISSUE AL



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

Notes

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